

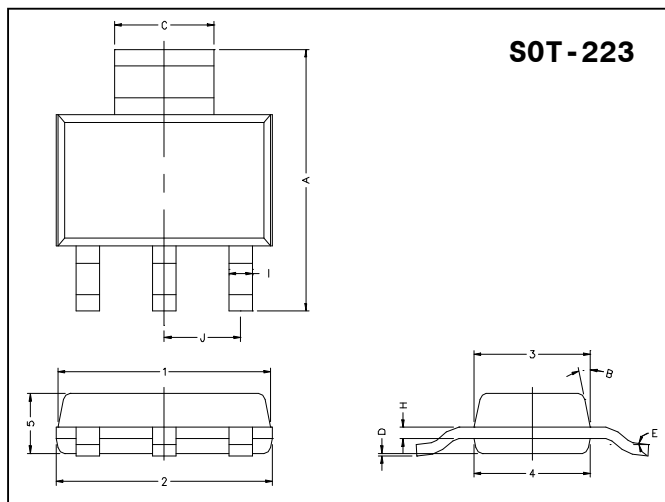
GL3019

NPN EPITAXIAL PLANAR TRANSISTOR

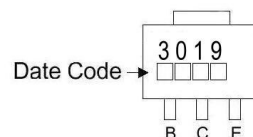
Description

The GL3019 is designed for general purpose amplifier applications and switching requiring collector currents 1A.

Package Dimensions



Marking :



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	6.70	7.30	B	13° TYP.	
C	2.90	3.10	J	2.30 REF.	
D	0.02	0.10	1	6.30	6.70
E	0°	10°	2	6.30	6.70
I	0.60	0.80	3	3.30	3.70
H	0.25	0.35	4	3.30	3.70
			5	1.40	1.80

Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Ratings	Unit
Junction Temperature	Tj	+150	°C
Storage Temperature	Tstg	-55 ~ +150	°C
Collector to Base Voltage	VCBO	140	V
Collector to Emitter Voltage	VCEO	80	V
Emitter to Base Voltage	VEBO	7	V
Collector Current	IC	1	A
Total Power Dissipation	PD	2	W

Characteristics at Ta = 25°C

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BVCBO	140	-	-	V	IC=100uA
BVCEO	80	-	-	V	IC=30mA
BVEBO	7	-	-	V	IE=100uA
ICBO	-	-	50	nA	VCB=90V
IEBO	-	-	50	nA	VEB=5V
VCE(sat)	-	-	0.2	V	IC=150mA, IB=15mA
VBE(sat)	-	-	1.1	V	IC=150mA, IB=15mA
hFE1	50	-	-		VCE=10V, IC=0.1mA
hFE2	90	-	-		VCE=10V, IC=10mA
hFE3	100	-	300		VCE=10V, IC=150mA
hFE4	50	-	-		VCE=10V, IC=500mA
hFE5	15	-	-		VCE=10V, IC=1000mA
fT	100	-	-	MHz	VCE=50mV, IC=50mA, f=100MHz
Cob	-	-	12	pF	VCE=10V, IE=0, f=1MHz

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